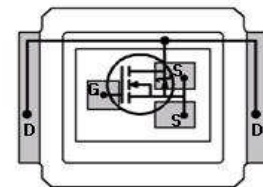


**OptiMOS™3 Power-MOSFET**
**Features**

- Optimized technology for DC/DC converters
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Superior thermal resistance
- Dual sided cooling
- low parasitic inductance
- Low profile (<0.7mm)
- N-channel, normal level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Compatible with DirectFET® package MN footprint and outline<sup>2)</sup>

**Product Summary**

$V_{DS}$	80	V
$R_{DS(on),max}$	4.4	m $\Omega$
$I_D$	90	A

**CanPAK™ M  
MG-WDSO-2**


Type	Package	Outline	Marking
BSB044N08NN3 G	MG-WDSO-2	MN	0208

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$V_{GS}=10\text{ V}, T_C=25\text{ °C}$	90	A
		$V_{GS}=10\text{ V}, T_C=100\text{ °C}$	68	
		$V_{GS}=10\text{ V}, T_A=25\text{ °C}, R_{thJA}=58\text{ K/W}^{2)}$	18	
Pulsed drain current <sup>3)</sup>	$I_{D,pulse}$	$T_C=25\text{ °C}$	360	
Avalanche energy, single pulse	$E_{AS}$	$I_D=30\text{ A}, R_{GS}=25\text{ }\Omega$	660	mJ
Gate source voltage	$V_{GS}$		$\pm 20$	V

<sup>1)</sup> J-STD20 and JESD22

<sup>2)</sup> DirectFET® is a trademark of International Rectifier Corporation

BSB028N06NN3 G uses DirectFET® technology licensed from International Rectifier Corporation

**Maximum ratings**, at  $T_j=25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Power dissipation	$P_{\text{tot}}$	$T_C=25\text{ °C}$	78	W
		$T_A=25\text{ °C}$ , $R_{\text{thJA}}=58\text{ K/W}^2)$	2.2	
Operating and storage temperature	$T_j, T_{\text{stg}}$		-40 ... 150	°C
IEC climatic category; DIN IEC 68-1			55/150/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

### Thermal characteristics

Thermal resistance, junction - case	$R_{\text{thJC}}$	bottom	-	1.0	-	K/W
		top	-	-	1.6	
Device on PCB	$R_{\text{thJA}}$	6 cm <sup>2</sup> cooling area <sup>2)</sup>	-	-	58	

**Electrical characteristics**, at  $T_j=25\text{ °C}$ , unless otherwise specified

### Static characteristics

Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}}=0\text{ V}$ , $I_{\text{D}}=1\text{ mA}$	80	-	-	V
Gate threshold voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}$ , $I_{\text{D}}=97\text{ }\mu\text{A}$	2	2.8	3.5	
Zero gate voltage drain current	$I_{\text{DSS}}$	$V_{\text{DS}}=80\text{ V}$ , $V_{\text{GS}}=0\text{ V}$ , $T_j=25\text{ °C}$	-	0.1	10	$\mu\text{A}$
		$V_{\text{DS}}=80\text{ V}$ , $V_{\text{GS}}=0\text{ V}$ , $T_j=125\text{ °C}$	-	10	100	
Gate-source leakage current	$I_{\text{GSS}}$	$V_{\text{GS}}=20\text{ V}$ , $V_{\text{DS}}=0\text{ V}$	-	10	100	nA
Drain-source on-state resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}}=10\text{ V}$ , $I_{\text{D}}=30\text{ A}$	-	3.7	4.4	
Gate resistance	$R_{\text{G}}$		-	0.5	-	$\Omega$
Transconductance	$g_{\text{fs}}$	$ V_{\text{DS}} >2 I_{\text{D}} R_{\text{DS(on)max}}$ , $I_{\text{D}}=30\text{ A}$	36	72	-	S

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical in still air.

<sup>3)</sup> See figure 3 for more detailed information

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=40\text{ V}, f=1\text{ MHz}$	-	4300	5700	pF
Output capacitance	$C_{oss}$		-	1100	1450	
Reverse transfer capacitance	$C_{rss}$		-	38	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=40\text{ V}, V_{GS}=10\text{ V}, I_D=30\text{ A}, R_G=1.6\ \Omega$	-	14	-	ns
Rise time	$t_r$		-	9	-	
Turn-off delay time	$t_{d(off)}$		-	26	-	
Fall time	$t_f$		-	7	-	

**Gate Charge Characteristics<sup>5)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=40\text{ V}, I_D=30\text{ A}, V_{GS}=0\text{ to }10\text{ V}$	-	17	-	nC
Gate to drain charge	$Q_{gd}$		-	11	-	
Switching charge	$Q_{sw}$		-	17	-	
Gate charge total	$Q_g$		-	55	73	
Gate plateau voltage	$V_{plateau}$		-	4.6	-	V
Output charge	$Q_{oss}$	$V_{DD}=30\text{ V}, V_{GS}=0\text{ V}$	-	75	99	

**Reverse Diode**

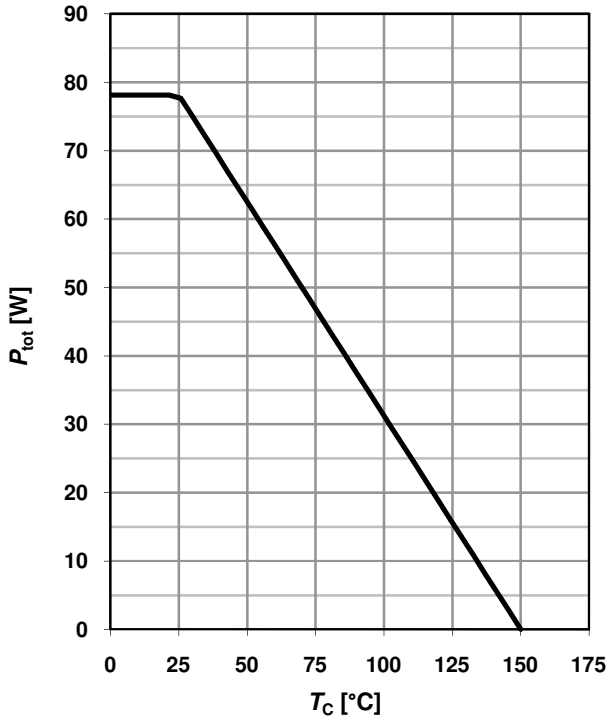
Diode continuous forward current	$I_S$	$T_C=25\text{ }^\circ\text{C}$	-	-	30	A
Diode pulse current	$I_{S,pulse}$		-	-	120	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=30\text{ A}, T_J=25\text{ }^\circ\text{C}$	-	0.9	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=40\text{ V}, I_F=I_S, di_F/dt=400\text{ A}/\mu\text{s}$	-	55	-	ns
Reverse recovery charge	$Q_{rr}$		-	110	-	

<sup>4)</sup> See figure 13 for more detailed information

<sup>5)</sup> See figure 16 for gate charge parameter definition

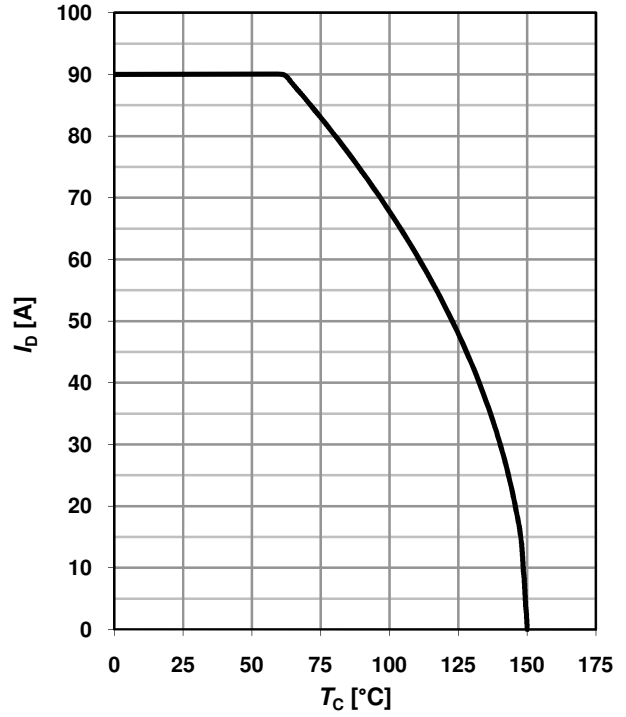
**1 Power dissipation**

$P_{tot}=f(T_C)$



**2 Drain current**

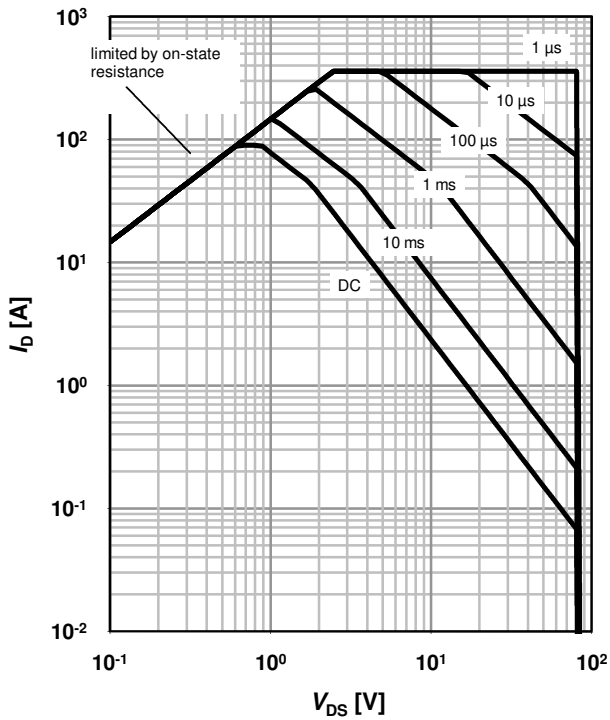
$I_D=f(T_C); V_{GS} \geq 10\text{ V}$



**3 Safe operating area**

$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$

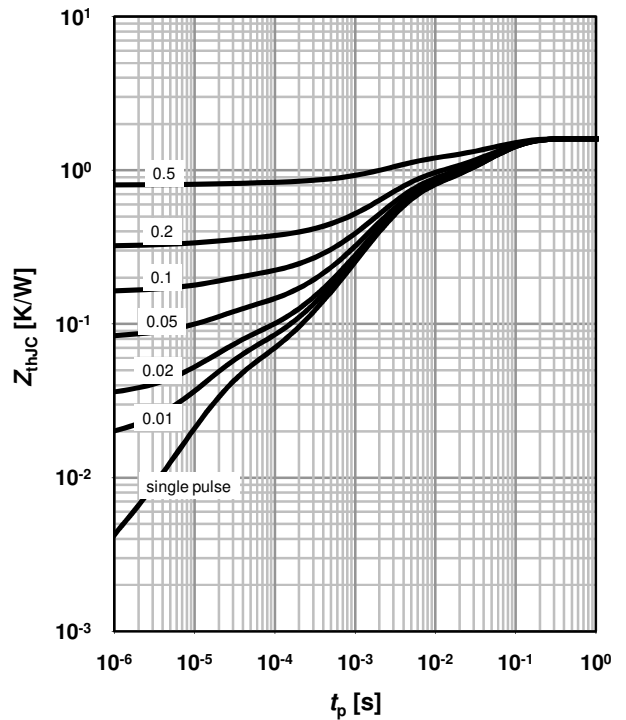
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJC}=f(t_p)$

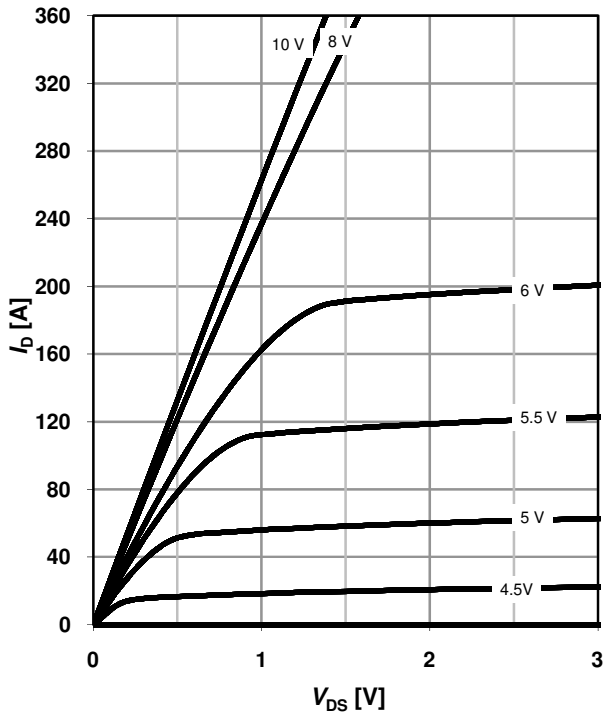
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ °C}$

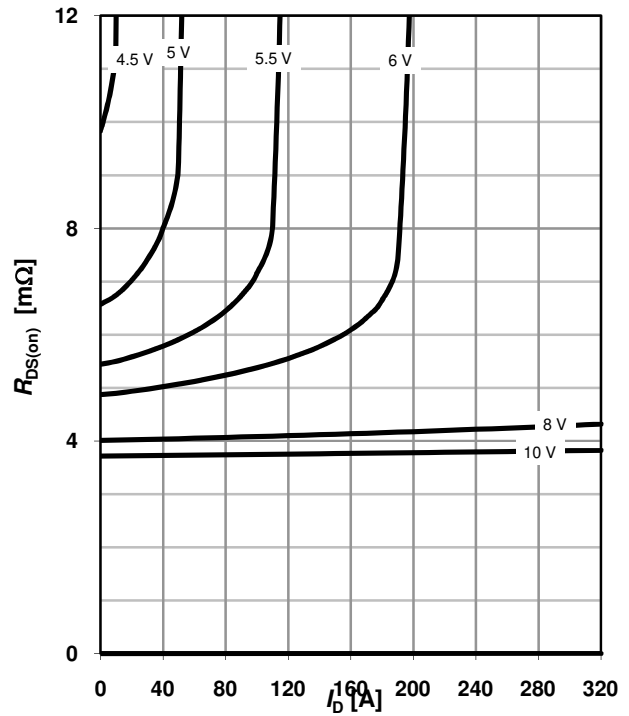
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ °C}$

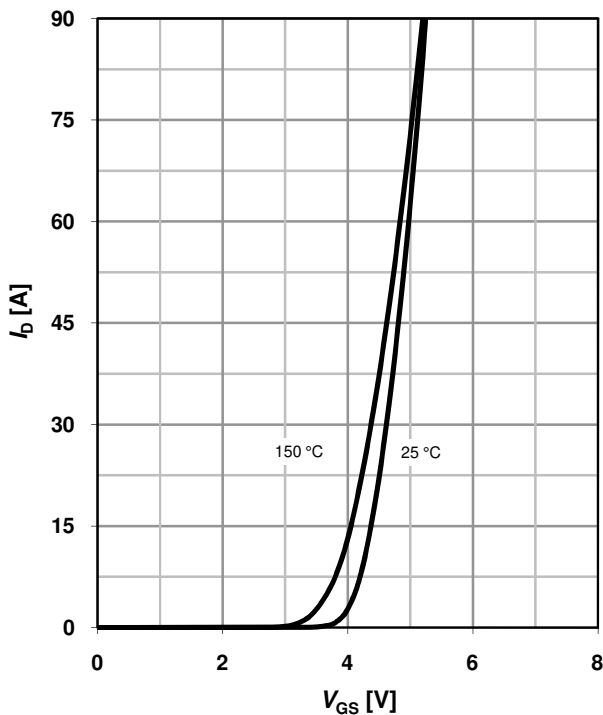
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

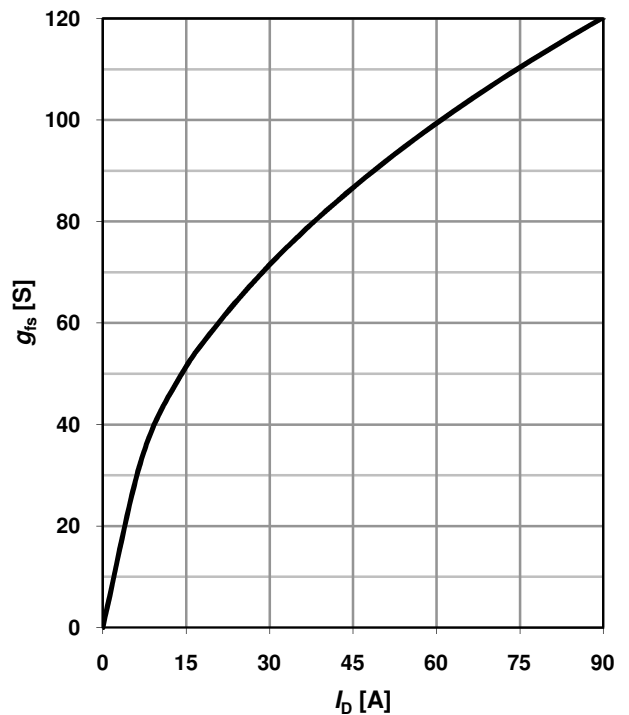
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter:  $T_j$



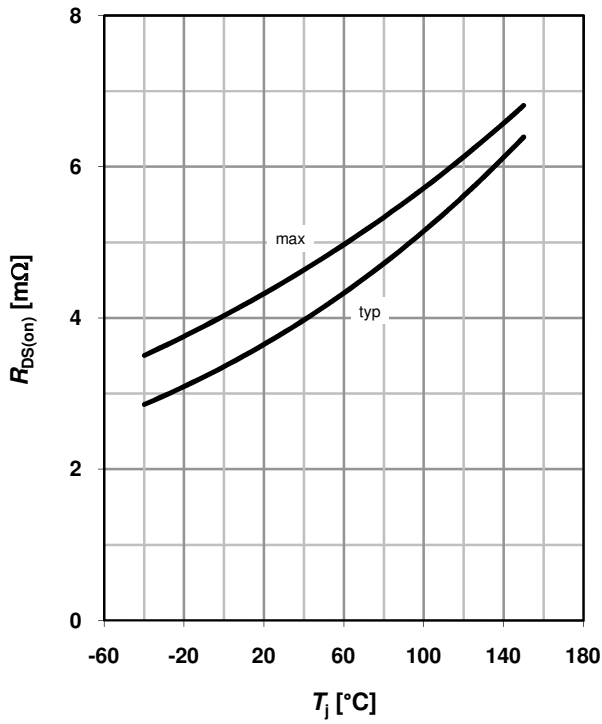
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ °C}$



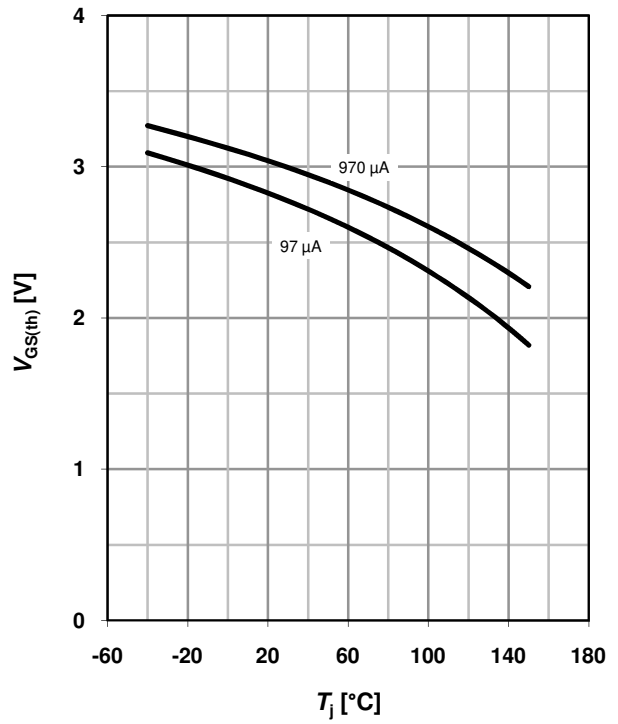
**9 Drain-source on-state resistance**

$R_{DS(on)}=f(T_j); I_D=30\text{ A}; V_{GS}=10\text{ V}$



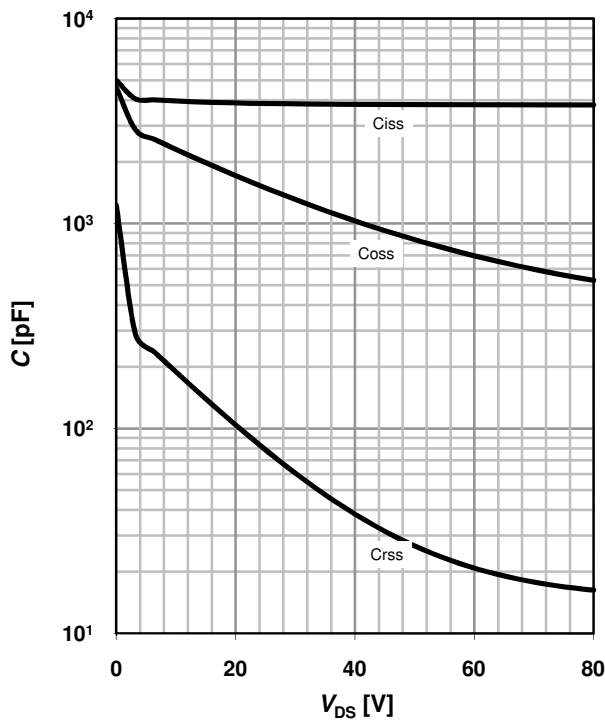
**10 Typ. gate threshold voltage**

$V_{GS(th)}=f(T_j); V_{GS}=V_{DS}$



**11 Typ. capacitances**

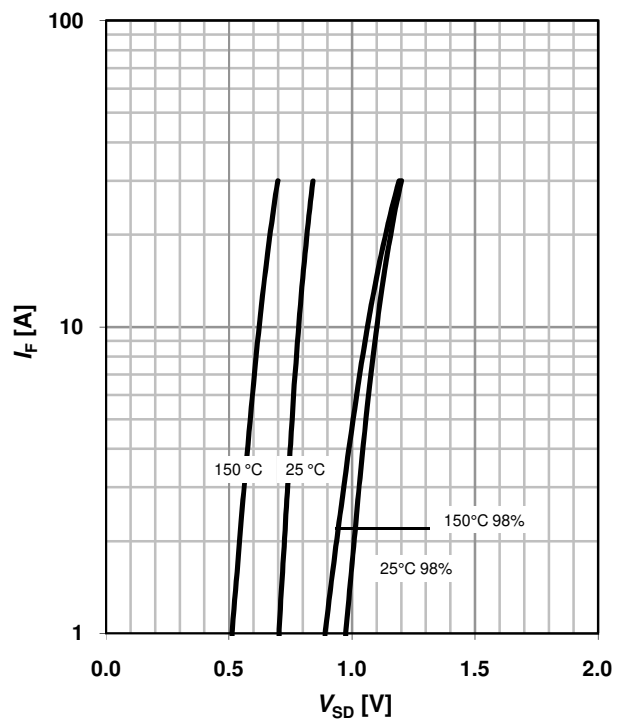
$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F=f(V_{SD})$

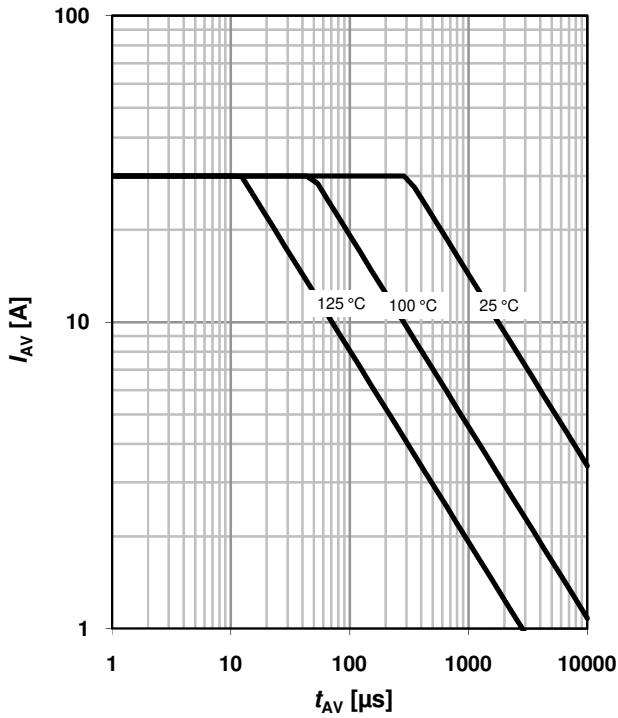
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

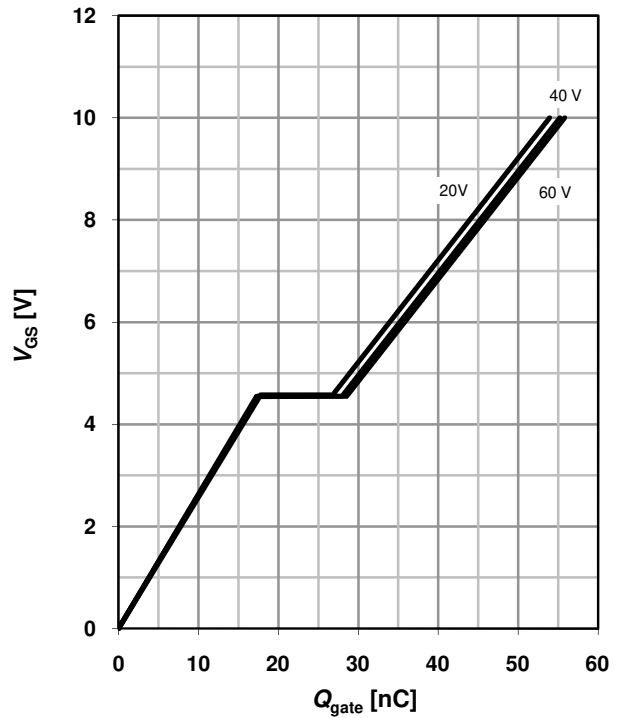
parameter:  $T_{j(\text{start})}$



**14 Typ. gate charge**

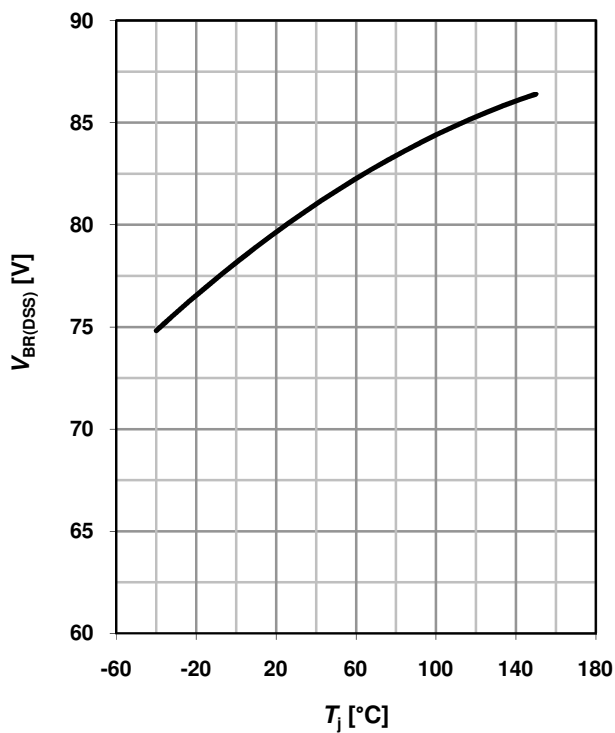
$V_{GS}=f(Q_{\text{gate}}); I_D=30 \text{ A pulsed}$

parameter:  $V_{DD}$

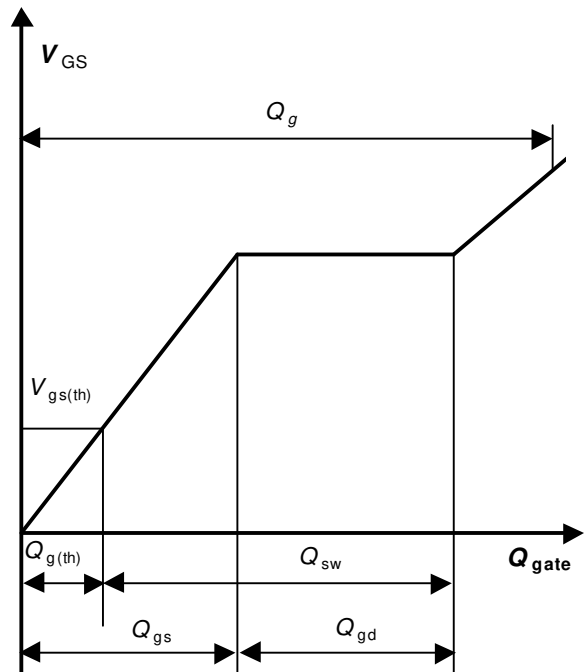


**15 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

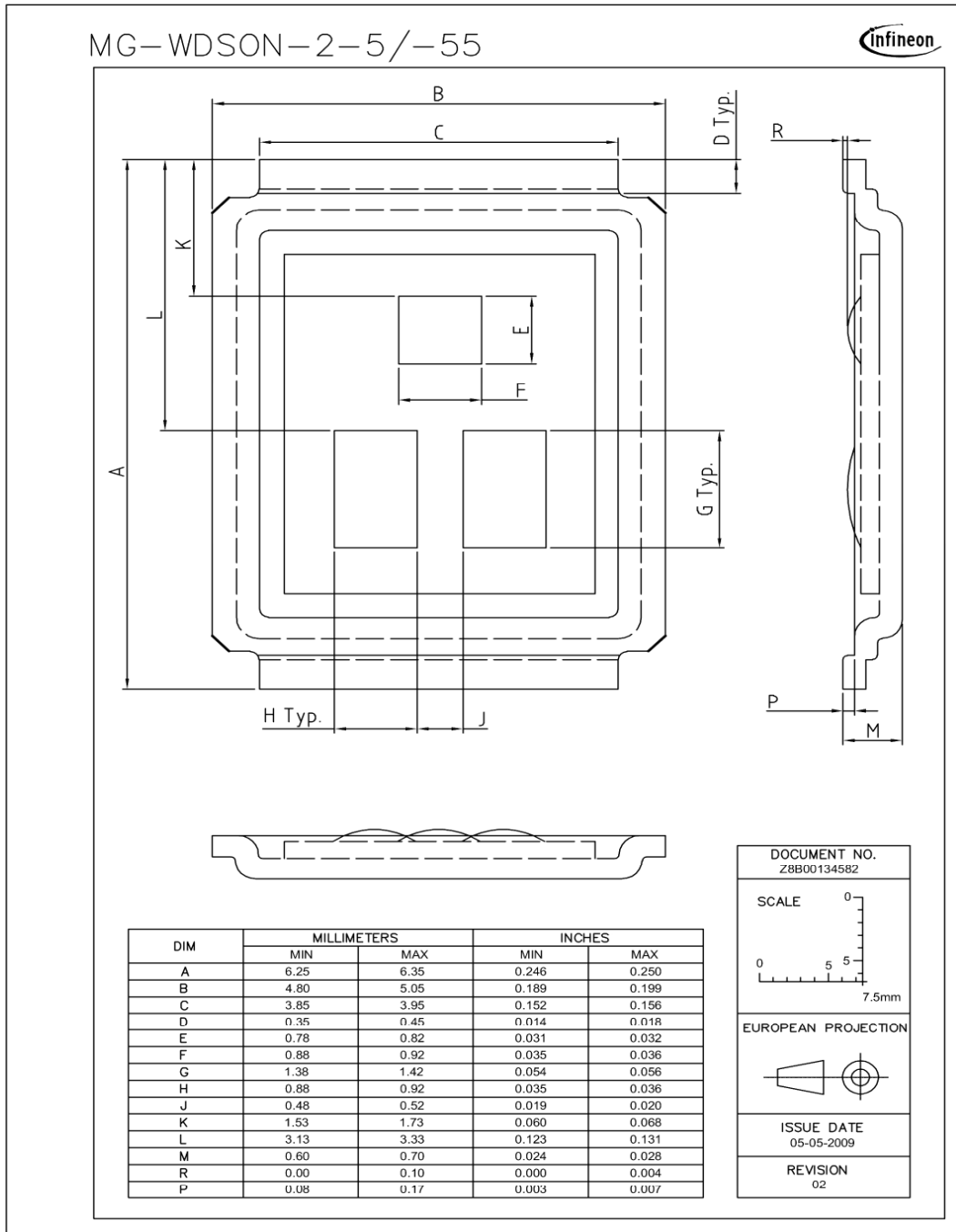


**16 Gate charge waveforms**



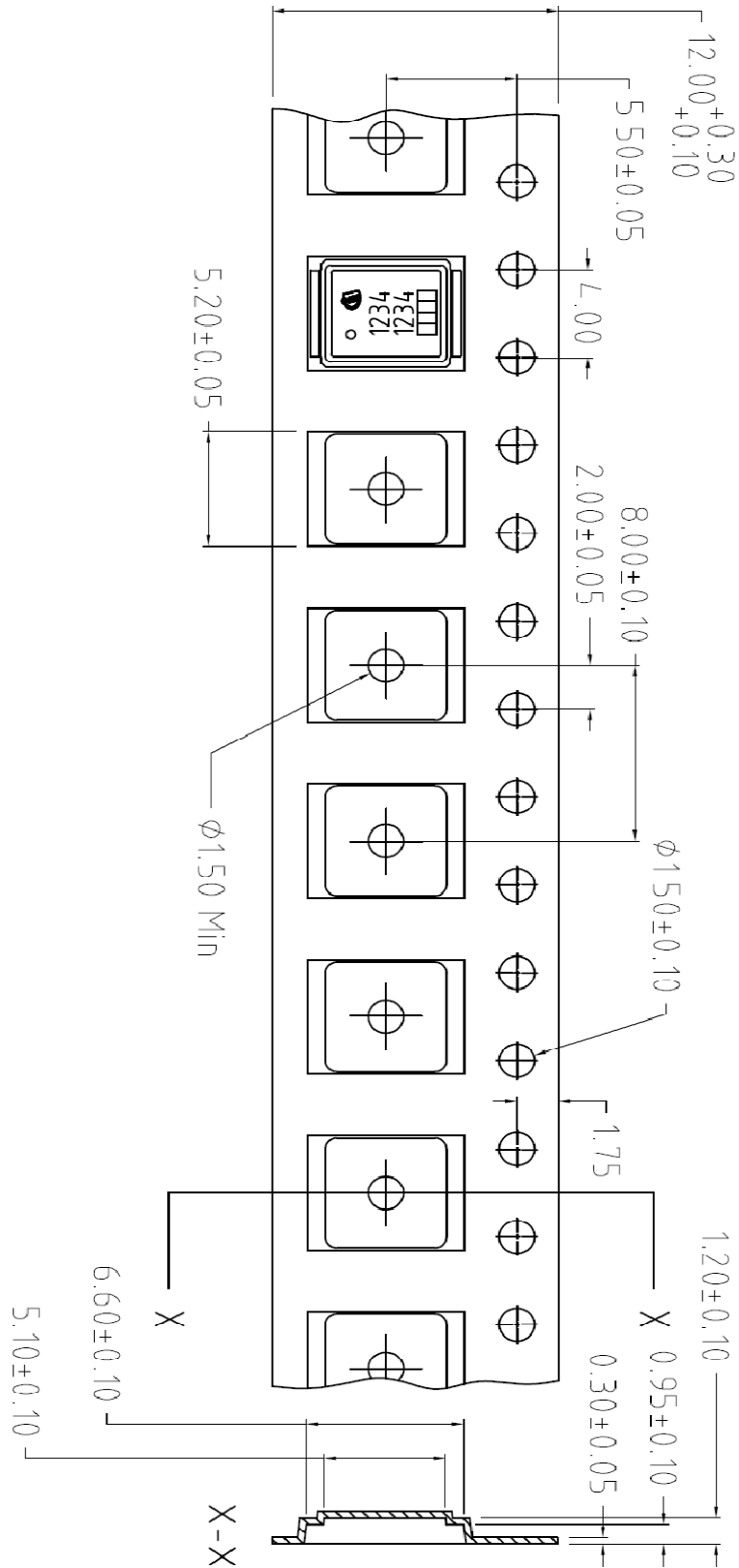
Package Outline

CanPAK™ M  
MG-WDSO-2



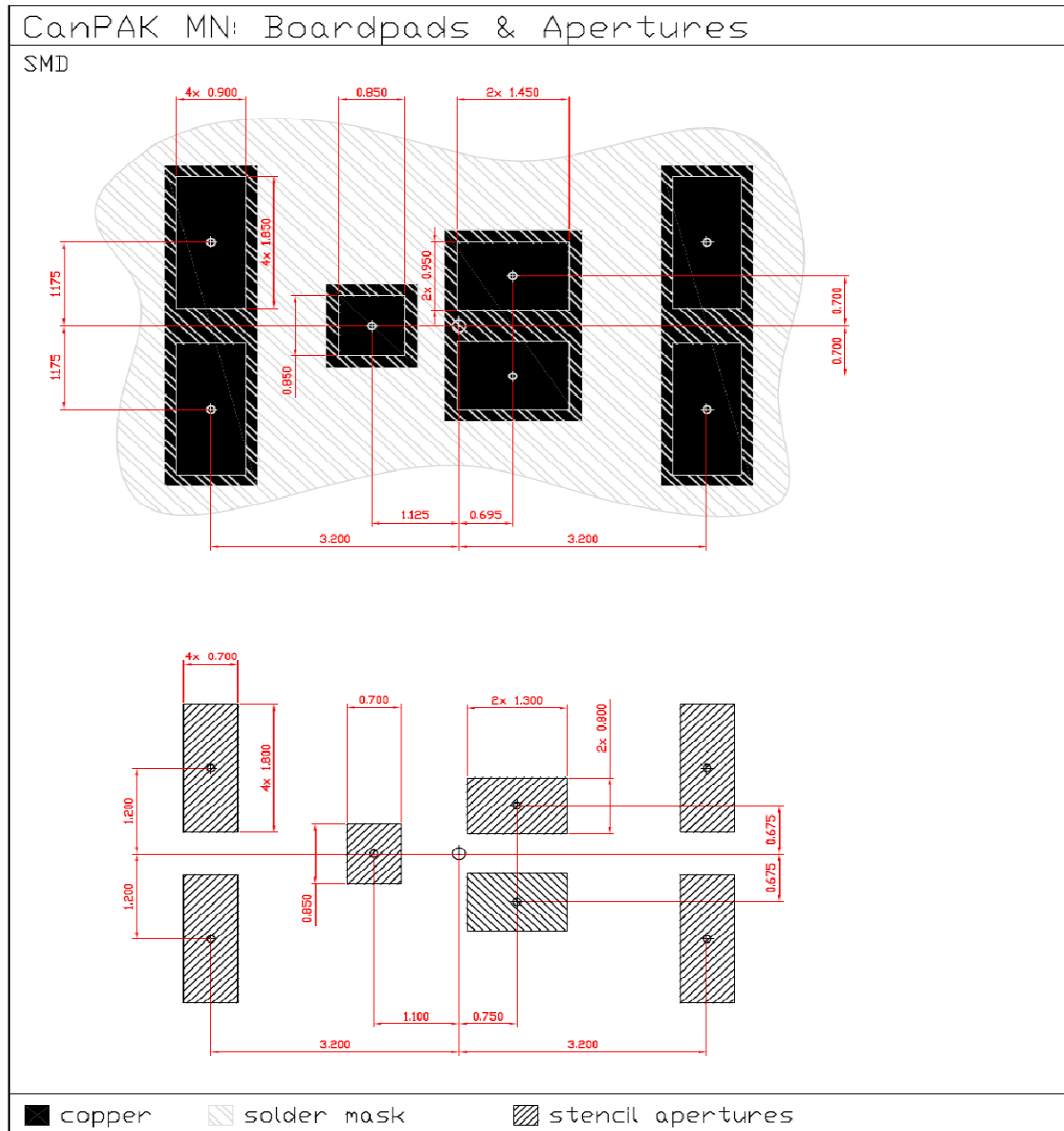


**CanPAK™ M**  
**MG-WDSO-2**



Dimensions in mm

CanPAK™ M  
MG-WDSO-2



Dimensions in mm

Raccomended stencil thickness 150 µm

**Published by**

**Infineon Technologies AG**  
**81726 Munich, Germany**  
**© 2011 Infineon Technologies AG**  
**All Rights Reserved.**

**Legal Disclaimer**

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

**Information**

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office ([www.infineon.com](http://www.infineon.com)).

**Warnings**

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.